

MOSFETs Silicon Carbide N-Channel MOS

# TW027N65C

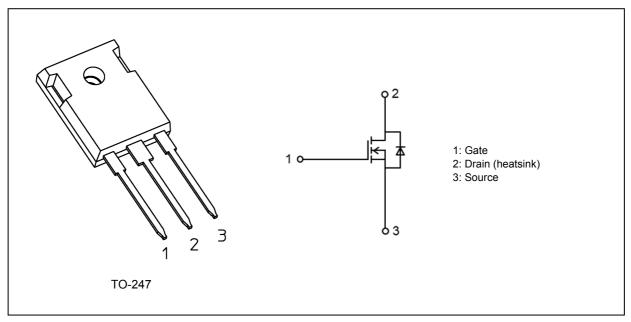
### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage:  $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage:  $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 27 \text{ m}\Omega$  (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage:  $V_{th} = 3.0$  to 5.0 V ( $V_{DS} = 10$  V,  $I_D = 3$  mA)
- (6) Recommended gate source drive voltage:  $V_{GS\_on} = 18 \text{ V}$ ,  $V_{GS\_off} = 0 \text{ V}$
- (7) Enhancement mode.

### 3. Packaging and Internal Circuit





# 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

|                        | Characteristics            | Symbol           | Rating     | Unit  |
|------------------------|----------------------------|------------------|------------|-------|
| Drain-source voltage   |                            | $V_{DSS}$        | 650        | V     |
| Gate-source voltage    |                            | $V_{GSS}$        | +25/-10    |       |
| Drain current (DC)     | ( T <sub>c</sub> = 25 °C ) | $I_{D}$          | 58         | Α     |
| Drain current (DC)     | ( T <sub>c</sub> = 100°C ) | $I_D$            | 42         |       |
| Drain current (pulsed) | ( T <sub>c</sub> = 25 °C ) | I <sub>DP</sub>  | 170        |       |
| Drain current (pulsed) | ( T <sub>c</sub> = 100°C ) | I <sub>DP</sub>  | 128        |       |
| Power dissipation      | ( T <sub>c</sub> = 25°C )  | P <sub>D</sub>   | 156        | W     |
| Channel temperature    |                            | T <sub>ch</sub>  | 175        | °C    |
| Storage temperature    |                            | T <sub>stg</sub> | -55 to 175 |       |
| Mounting torque        |                            | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 0.961 | °C/W |
| Channel-to-ambient thermal resistance |                       | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|--|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | V <sub>GS</sub> = +25/-10 V, V <sub>DS</sub> = 0 V                         | _   | _    | ±0.1 | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V                             | _   | 7    | 100  |      |
|                                |                      | T <sub>a</sub> = 150 °C,<br>V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V | _   | 37   | ı    |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 4 mA, V <sub>GS</sub> = 0 V                               | 650 | _    | _    | V    |
| Gate threshold voltage (Not    | e 2) V <sub>th</sub> | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 mA                              | 3.0 | _    | 5.0  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 18 V, I <sub>D</sub> = 29 A                              | _   | 27   | 37   | mΩ   |
|                                |                      | $T_a$ = 150 °C,<br>$V_{GS}$ = 18 V, $I_D$ = 29 A                           | _   | 31   |      |      |

Note 2: Please be sure to apply  $I_{GSS}$  ( $V_{GS}$  = 25 V) before the  $V_{th}$  test.

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                               | Symbol             | Test Condition                                  | Min | Тур. | Max | Unit |
|---|--------------------|---|-----|------|-----|------|
| Input capacitance                             | C <sub>iss</sub>   | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, | _   | 2288 | _   | pF   |
| Reverse transfer capacitance                  | C <sub>rss</sub>   | f = 100 kHz                                     | _   | 6.6  | _   |      |
| Output capacitance                            | C <sub>oss</sub>   | 1   | _   | 249  | _   |      |
| Effective output capacitance (energy related) | C <sub>o(er)</sub> |   | _   | 288  | _   |      |
| Effective output capacitance (time related)   | C <sub>o(tr)</sub> |   | _   | 413  | _   |      |
| Output charge                                 | Q <sub>oss</sub>   | 7   | _   | 165  | _   | nC   |
| C <sub>oss</sub> stored energy                | E <sub>oss</sub>   | 1   | _   | 23   | _   | μJ   |
| Gate resistance                               | r <sub>g</sub>     | V <sub>DS</sub> = OPEN, f = 1 MHz               | _   | 2.1  | _   | Ω    |
| Switching time (rise time)                    | t <sub>r</sub>     | See Fig. 6.2.1                                  | _   | 50   | _   | ns   |
| Switching time (turn-on time)                 | t <sub>on</sub>    | 1   | _   | 80   | _   |      |
| Switching time (fall time)                    | t <sub>f</sub>     | 1   | _   | 40   | _   |      |
| Switching time (turn-off time)                | t <sub>off</sub>   | 1   | _   | 83   | _   | ns   |

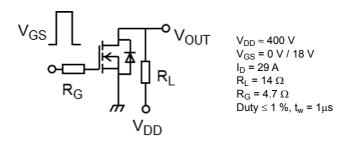


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$<br>$I_{D} = 29 \text{ A}$ | _   | 65   |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 26   |     |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 10   | _   |      |



# 6.4. Source $\cdot$ Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics               |          | Symbol           | Test Condition   | Min | Тур.  | Max   | Unit |
|-------------------------------|----------|------------------|--|-----|-------|-------|------|
| Reverse drain current (DC)    | (Note 3) | I <sub>DR</sub>  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V                             | _   | _     | 44    | Α    |
|                               |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V                            | _   | _     | 29    |      |
|                               |          |                  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V                             | _   | _     | 58    |      |
|                               |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V                            | _   | _     | 42    |      |
| Reverse drain current         | (Note 3) | I <sub>DRP</sub> | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V                             | _   | _     | 163   |      |
| (pulsed)                      |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V                            | _   | _     | 75    |      |
|                               |          |                  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V                             | _   | _     | 170   |      |
|                               |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V                            | _   | _     | 128   |      |
| Diode forward voltage         |          | V <sub>DSF</sub> | I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V                             | _   | -1.35 | -1.80 | V    |
|                               |          |                  | T <sub>a</sub> = 150 °C,<br>I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V | _   | -1.57 | _     |      |
| Reverse recovery time         |          | t <sub>rr</sub>  | I <sub>DR</sub> = 19 A, V <sub>GS</sub> = 0 V,                             | _   | 55    | _     | ns   |
| Reverse recovery charge       |          | Q <sub>rr</sub>  | $V_{DD} = 400 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$         | _   | 358   | _     | nC   |
| Peak reverse recovery current |          | I <sub>rr</sub>  |  | _   | 13    | _     | Α    |

Note 3: Ensure that the channel temperature does not exceed 175 °C.



# 7. Marking (Note)

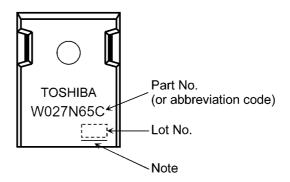


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS

compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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### 8. Characteristics Curves (Note)

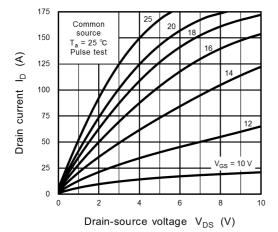


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

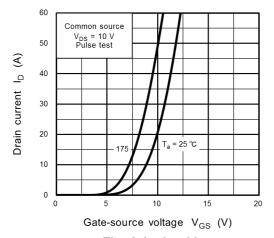


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

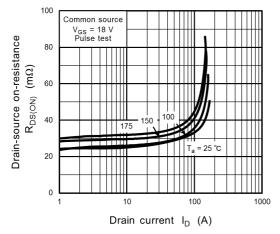


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

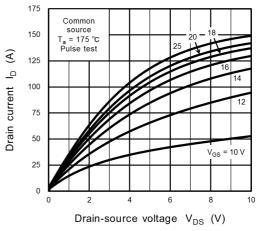


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

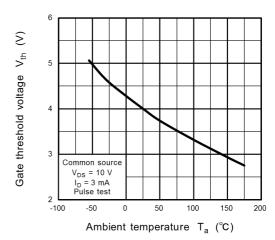


Fig. 8.4 V<sub>th</sub> - T<sub>a</sub>

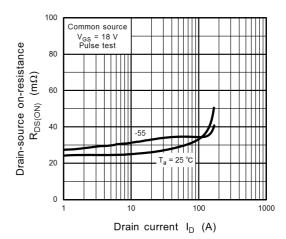


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>



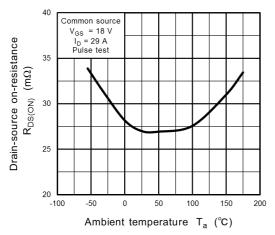


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

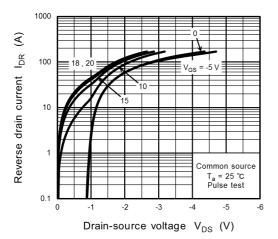


Fig. 8.9 IDR - VDS

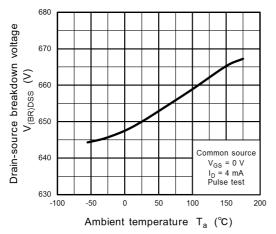


Fig. 8.11 V<sub>DSS</sub> - T<sub>a</sub>

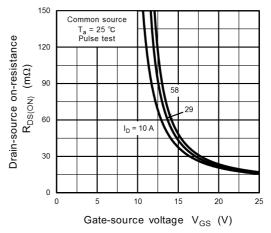


Fig. 8.8 R<sub>DS(ON)</sub> - V<sub>GS</sub>

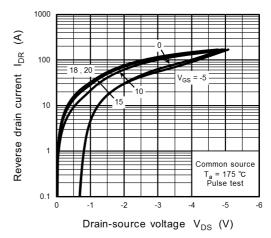


Fig. 8.10 I<sub>DR</sub> - V<sub>DS</sub>

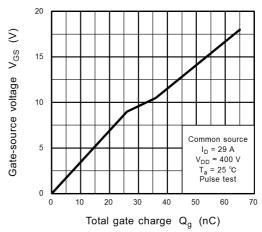
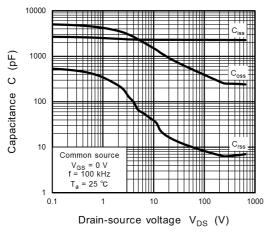


Fig. 8.12 Dynamic Input Characteristics

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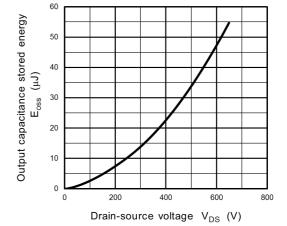


Fig. 8.13 C - V<sub>DS</sub>

Fig. 8.14 Eoss - VDS

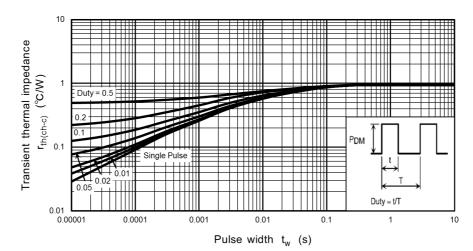
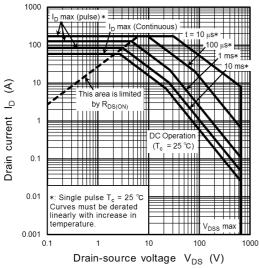


Fig. 8.15  $r_{th(ch-c)} - t_w$  (Guaranteed Maximum)



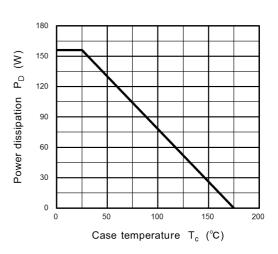


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

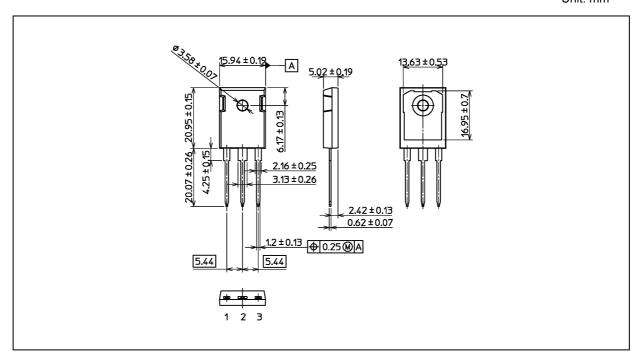
Fig. 8.17 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 6.15 g (typ.)

| Package Name(s)  |
|------------------|
| TOSHIBA: 2-16L1A |
| Nickname: TO-247 |



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